DG2012E

## Powered-off Protection, $1 \Omega, 1.8 \mathrm{~V}$ to 5.5 V , SPDT Analog Switch (2:1 Multiplexer)

## DESCRIPTION

The DG2012E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of $1 \Omega$ at a 5 V power supply, low power consumption, and fast switching speeds.
The DG2012E can handle both analog and digital signals and permits signals with amplitudes of up to $V+$ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V . It features break before make switching performance. Its -3 dB bandwidth is typically 160 MHz . A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to $\mathrm{V}+$ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).
Operation temperature is specified from $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$. The DG2012E is available in SC-70-6L package.

## FEATURES

- Low switch on-resistance ( $1 \Omega$ )
- 1.65 V to 5.5 V single supply operation

- Isolation in powered-off mode
- Control logic inputs can go over V+
- Low charge injection (5 pC)
- Low total harmonic distortion
- Break before make switching
- Latch-up performance exceeds 300 mA per JESD 78
- ESD tested
- 7000 V human body model (JS-001)
- 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


## Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead ( Pb ) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details


## APPLICATIONS

- Smartphones and tablets
- Consumer and computing
- Portable instrumentation
- Medical equipment


## FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION




Device marking: H2XXX
XXX = date / lot traceability code

## TRUTH TABLE

| LOGIC | NC | NO |
| :---: | :---: | :---: |
| 0 | On | Off |
| 1 | Off | On |

ORDERING INFORMATION

| TEMP. RANGE | PACKAGE | PART NUMBER |
| :---: | :---: | :---: |
| $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ | SC-70-6 | DG2012EDL-T1-GE3 |

DG2012E

| ABSOLUTE MAXIMUM RATINGS |  |  |  |
| :---: | :---: | :---: | :---: |
| PARAMETER |  | LIMIT | UNIT |
| V+, COM, NC, NO, IN reference to GND |  | -0.3 to 6 | V |
| Continuous current (NO, NC, and COM pins) |  | $\pm 100$ | mA |
| Peak current (pulsed at $1 \mathrm{~ms}, 10 \%$ duty cycle) |  | $\pm 300$ |  |
| Storage temperature (D suffix) |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| Power dissipation (packages) ${ }^{\text {a }}$ | $6-\mathrm{pin} \mathrm{SO-70}{ }^{\text {b }}$ | 250 | mW |
| ESD / HBM | JS-001 | 7000 | V |
| ESD / CDM | JS-002 | 1000 |  |
| Latch up | Per JESD78 with $1.5 \times$ voltage clamp | 300 | mA |

## Notes

a. All leads welded or soldered to PC board
b. Derate $3.1 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ above $70^{\circ} \mathrm{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED $\mathrm{V}+=5 \mathrm{~V}, \pm 10 \%, \mathrm{~V}_{\text {IN }}=0.8 \mathrm{~V}$ or $2.4 \mathrm{~V}^{\mathrm{e}}$ | TEMP. ${ }^{\text {a }}$ | $\begin{gathered} \text { LIMITS } \\ -40^{\circ} \mathrm{C} \text { to }+85^{\circ} \mathrm{C} \end{gathered}$ |  |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | MIN. ${ }^{\text {b }}$ | TYP. ${ }^{\text {c }}$ | MAX. ${ }^{\text {b }}$ |  |
| Analog Switch |  |  |  |  |  |  |  |
| Analog signal range ${ }^{\text {d }}$ | $\mathrm{V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}$ $\mathrm{V}_{\text {COM }}$ |  | Full | 0 | - | V+ | V |
| On-resistance | Ron | $\begin{gathered} \mathrm{V}_{+}=4.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=0.5 \mathrm{~V} / 2.5 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 1 | 1.6 | $\Omega$ |
|  |  |  | Full ${ }^{\text {d }}$ | - |  | 2 |  |
| RoN flatness ${ }^{\text {d }}$ | $\begin{aligned} & \mathrm{R}_{\mathrm{ON}} \\ & \text { flatness } \end{aligned}$ | $\begin{gathered} \mathrm{V}_{+}=4.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=0 \mathrm{~V} \text { to } \mathrm{V}+, \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 0.2 | 0.5 |  |
| Ron match ${ }^{\text {d }}$ | $\Delta \mathrm{R}_{\text {ON }}$ |  | Room | - | - | 0.3 |  |
| Switch off leakage current ${ }^{\dagger}$ | $\mathrm{I}_{\mathrm{NO}}$ (off) $\mathrm{I}_{\mathrm{NC} \text { (off) }}$ | $\begin{gathered} \mathrm{V}+=5 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=0.5 \mathrm{~V} / 4.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=4.5 \mathrm{~V} / 0.5 \mathrm{~V} \end{gathered}$ | Room | -5 | - | 5 | nA |
|  |  |  | Full | -20 | - | 20 |  |
|  | ICOM(off) |  | Room | -5 | - | 5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -20 | - | 20 |  |
| Channel-on leakage current ${ }^{\dagger}$ | $\mathrm{ICOM}_{\text {(on) }}$ | $\begin{gathered} \mathrm{V}_{+}=5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{COM}}=0.5 \mathrm{~V} / 4.5 \mathrm{~V} \end{gathered}$ | Room | -5 | - | 5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -20 | - | 20 |  |
| Power down leakage | $\mathrm{I}_{\text {COM(PD) }}$ | $\mathrm{V}+=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=4.5 \mathrm{~V}, \mathrm{~V}_{\text {IN }}=\mathrm{GND}$ | Full ${ }^{\text {d }}$ | -1 | - | 1 | $\mu \mathrm{A}$ |
| Digital Control |  |  |  |  |  |  |  |
| Input high voltage | $\mathrm{V}_{\text {INH }}$ |  | Full | 2.4 | - | - | V |
| Input low voltage | $\mathrm{V}_{\text {INL }}$ |  | Full | - | - | 0.8 |  |
| Input capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\text {IN }}$ |  | Full | - | 3 | - | pF |
| Input current ${ }^{\text {f }}$ | $\mathrm{l}_{\mathrm{INL}}$ or $\mathrm{l}_{\mathrm{NH}}$ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | -1 | - | 1 | $\mu \mathrm{A}$ |
| Dynamic Characteristics |  |  |  |  |  |  |  |
| Turn-on time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{ON}}$ | $\begin{gathered} \mathrm{V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=3 \mathrm{~V}, \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \end{gathered}$ | Room | - | 15 | 32 | ns |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 35 |  |
| Turn-off time ${ }^{\text {d }}$ | toff |  | Room | - | 7 | 28 |  |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 30 |  |
| Break-before-make time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{d}}$ |  | Room | 1 | 5 | - |  |
| Charge injection ${ }^{\text {d }}$ | $\mathrm{Q}_{\text {INJ }}$ | $\mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega$ | Room | - | 8 | - | pC |
| Off-isolation ${ }^{\text {d }}$ | OIRR | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$ | Room | - | -63 | - | dB |
| Crosstalk ${ }^{\text {d }}$ | $\mathrm{X}_{\text {TALK }}$ |  | Room | - | -63 | - |  |
| $\mathrm{N}_{\mathrm{O}}, \mathrm{N}_{\mathrm{C}}$ off capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\mathrm{NO} \text { (off) }}$ $\mathrm{C}_{\mathrm{NC} \text { (off) }}$ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}+\mathrm{f}=1 \mathrm{MHz}$ | Room | - | 16 | - | pF |
| Channel-on capacitance ${ }^{\text {d }}$ | $\mathrm{Con}^{\text {N }}$ |  | Room | - | 52 | - |  |
| Power Supply |  |  |  |  |  |  |  |
| Power supply current | I+ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | - | 0.0003 | 1 | $\mu \mathrm{A}$ |


| SPECIFICATIONS (V+ = 3 V ) |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED $\mathrm{V}+=3 \mathrm{~V}, \pm 10 \%, \mathrm{~V}_{\text {IN }}=0.4 \mathrm{~V}$ or 1.4 V e | TEMP. ${ }^{\text {a }}$ | LIMITS <br> $-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$ |  |  | UNIT |
|  |  |  |  | MIN. ${ }^{\text {b }}$ | TYP. ${ }^{\text {c }}$ | MAX. ${ }^{\text {b }}$ |  |
| Analog Switch |  |  |  |  |  |  |  |
| Analog signal range ${ }^{\text {d }}$ | $\begin{gathered} \hline \mathrm{V}_{\mathrm{NO},}, \mathrm{~V}_{\mathrm{NC}} \\ \mathrm{~V}_{\mathrm{COM}} \end{gathered}$ |  | Full | 0 | - | V+ | V |
| On-resistance | Ron | $\begin{gathered} \mathrm{V}_{+}=2.7 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=0.2 \mathrm{~V} / 1.5 \mathrm{~V}, \mathrm{I}_{\mathrm{NO}} \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 1.4 | 2.5 | $\Omega$ |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 3 |  |
| RoN flatness ${ }^{\text {d }}$ | $\begin{aligned} & \mathrm{R}_{\mathrm{ON}} \\ & \text { flatness } \end{aligned}$ | $\begin{gathered} \mathrm{V}_{+}=2.7 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=0 \mathrm{~V} \text { to } \mathrm{V}+, \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 0.6 | 0.9 |  |
| RoN match ${ }^{\text {d }}$ | $\Delta \mathrm{R}_{\text {ON }}$ |  | Room | - | - | 0.3 |  |
| Switch off leakage current ${ }^{\dagger}$ | $\mathrm{I}_{\mathrm{NO} \text { (off) }}$ $\mathrm{I}_{\mathrm{NC} \text { (off) }}$ | $\begin{gathered} \mathrm{V}_{+}=3.3 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=1 \mathrm{~V} / 3 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=3 \mathrm{~V} / 1 \mathrm{~V} \end{gathered}$ | Room | -5 | - | 5 | nA |
|  |  |  | Full | -15 | - | 15 |  |
|  | $\mathrm{I}_{\text {com(fff) }}$ |  | Room | -5 | - | 5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -15 | - | 15 |  |
| Channel-on leakage current ${ }^{\dagger}$ | ICOM(on) | $\begin{gathered} \mathrm{V}+=3.3 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{COM}}=1 \mathrm{~V} / 3 \mathrm{~V} \end{gathered}$ | Room | -5 | - | 5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -15 | - | 15 |  |
| Digital Control |  |  |  |  |  |  |  |
| Input high voltage | $\mathrm{V}_{\text {INH }}$ |  | Full | 1.4 | - | - | V |
| Input low voltage | $\mathrm{V}_{\text {INL }}$ |  | Full | - | - | 0.4 |  |
| Input capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\text {IN }}$ |  | Full | - | 3 | - | pF |
| Input current ${ }^{\dagger}$ | $\mathrm{I}_{\text {INL }}$ or $\mathrm{I}_{\text {INH }}$ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | -1 | - | 1 | $\mu \mathrm{A}$ |
| Dynamic Characteristics |  |  |  |  |  |  |  |
| Turn-on time ${ }^{\text {d }}$ | ton | $\begin{gathered} \mathrm{V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=2 \mathrm{~V}, \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \end{gathered}$ | Room | - | 21 | 42 | ns |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 47 |  |
| Turn-off time ${ }^{\text {d }}$ | toff |  | Room | - | 16 | 32 |  |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 35 |  |
| Break-before-make time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{d}}$ |  | Room | 1 | 7 | - |  |
| Charge injection ${ }^{\text {d }}$ | $\mathrm{Q}_{\text {INJ }}$ | $\mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega$ | Room | - | 6 | - | pC |
| Off-isolation ${ }^{\text {d }}$ | OIRR | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$ | Room | - | -63 | - | dB |
| Crosstalk ${ }^{\text {d }}$ | $\mathrm{X}_{\text {TALK }}$ |  | Room | - | -63 | - |  |
| Bandwidth ${ }^{\text {d }}$ | BW |  | Room | - | 160 | - | MHz |
| $\mathrm{N}_{\mathrm{O}}, \mathrm{N}_{\mathrm{C}}$ off capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\mathrm{NO} \text { (off) }}$ $\mathrm{C}_{\mathrm{NC} \text { (off) }}$ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}+\mathrm{f}=1 \mathrm{MHz}$ | Room | - | 16 | - | pF |
| Channel-on capacitance ${ }^{\text {d }}$ | CoN |  | Room | - | 52 | - |  |
| Power Supply |  |  |  |  |  |  |  |
| Power supply current | I+ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | - | 0.00002 | 1 | $\mu \mathrm{A}$ |

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| SPECIFICATIONS (V+ = 2 V ) |  |  |  |  |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED $\mathrm{V}+=2 \mathrm{~V}, \pm 10 \%, \mathrm{~V}_{\mathrm{IN}}=0.4 \mathrm{~V}$ or $1.6 \mathrm{~V}{ }^{\mathrm{e}}$ | TEMP. ${ }^{\text {a }}$ | $\begin{aligned} & \text { LIMITS } \\ & -40^{\circ} \mathrm{C} \text { to }+85^{\circ} \mathrm{C} \end{aligned}$ |  |  | UNIT |
|  |  |  |  | MIN. ${ }^{\text {b }}$ | TYP. ${ }^{\text {c }}$ | MAX. ${ }^{\text {b }}$ |  |
| Analog Switch |  |  |  |  |  |  |  |
| Analog signal range ${ }^{\text {d }}$ | $\begin{gathered} \mathrm{V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}, \\ \mathrm{~V}_{\mathrm{COM}} \\ \hline \end{gathered}$ |  | Full | 0 | - | V+ | V |
| On-resistance | $\mathrm{R}_{\mathrm{ON}}$ | $\begin{gathered} \mathrm{V}+=1.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=0.2 \mathrm{~V} / 0.9 \mathrm{~V} \\ \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 5 | 10 | $\Omega$ |
|  |  |  | Full d | - | - | 15 |  |
| RoN flatness ${ }^{\text {d }}$ | $\begin{aligned} & \mathrm{R}_{\mathrm{ON}} \\ & \text { flatness } \end{aligned}$ | $\begin{gathered} \mathrm{V}+=1.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{COM}}=0 \mathrm{~V} \text { to } \mathrm{V}+, \\ \mathrm{I}_{\mathrm{NO}}, \mathrm{I}_{\mathrm{NC}}=10 \mathrm{~mA} \end{gathered}$ | Room | - | 6 | 9 |  |
| Ron match ${ }^{\text {d }}$ | $\triangle \mathrm{R}_{\text {ON }}$ |  | Room | - | - | 0.3 |  |
| Switch off leakage current ${ }^{\dagger}$ | $\mathrm{I}_{\mathrm{NO} \text { (off) }}$ $\mathrm{I}_{\mathrm{NC} \text { (off) }}$ | $\begin{gathered} \mathrm{V}+=2.2 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=0.5 \mathrm{~V} / 1.5 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{COM}}=1.5 \mathrm{~V} / 0.5 \mathrm{~V} \end{gathered}$ | Room | -0.5 | - | 0.5 | nA |
|  |  |  | Full | -5 | - | 5 |  |
|  | $\mathrm{I}_{\text {COM (off) }}$ |  | Room | -0.5 | - | 0.5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -5 | - | 5 |  |
| Channel-on leakage current ${ }^{\text {f }}$ | $\mathrm{I}_{\text {COM(on) }}$ | $\begin{gathered} \mathrm{V}_{+}=2.2 \mathrm{~V}, \\ \mathrm{~V}_{\mathrm{NO}}, \mathrm{~V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{COM}}=0.5 \mathrm{~V} / 1.5 \mathrm{~V} \end{gathered}$ | Room | -0.5 | - | 0.5 |  |
|  |  |  | Full ${ }^{\text {d }}$ | -5 | - | 5 |  |
| Digital Control |  |  |  |  |  |  |  |
| Input high voltage | $\mathrm{V}_{\text {INH }}$ |  | Full | 1.6 | - | - | V |
| Input low voltage | $\mathrm{V}_{\text {INL }}$ |  | Full | - | - | 0.4 |  |
| Input capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\text {IN }}$ |  | Full | - | 3 | - | pF |
| Input current ${ }^{\text {f }}$ | $\mathrm{I}_{\mathrm{INL}}$ or $\mathrm{I}_{\text {INH }}$ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | -1 | - | 1 | $\mu \mathrm{A}$ |
| Dynamic Characteristics |  |  |  |  |  |  |  |
| Turn-on time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{ON}}$ | $\begin{gathered} \mathrm{V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=1.5 \mathrm{~V}, \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \end{gathered}$ | Room | - | 37 | 57 | ns |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 60 |  |
| Turn-off time ${ }^{\text {d }}$ | toff |  | Room | - | 26 | 44 |  |
|  |  |  | Full ${ }^{\text {d }}$ | - | - | 45 |  |
| Break-before-make time ${ }^{\text {d }}$ | $\mathrm{t}_{\mathrm{d}}$ |  | Room | 1 | 17 | - |  |
| Charge injection ${ }^{\text {d }}$ | Qinj | $\mathrm{C}_{\mathrm{L}}=1 \mathrm{nF}, \mathrm{V}_{\mathrm{GEN}}=0 \mathrm{~V}, \mathrm{R}_{\mathrm{GEN}}=0 \Omega$ | Room | - | 21 | - | pC |
| Off-isolation ${ }^{\text {d }}$ | OIRR | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5 \mathrm{pF}, \mathrm{f}=1 \mathrm{MHz}$ | Room | - | -63 | - | dB |
| Crosstalk ${ }^{\text {d }}$ | $\mathrm{X}_{\text {TALK }}$ |  | Room | - | -63 | - |  |
| $\mathrm{N}_{\mathrm{O}}, \mathrm{N}_{\mathrm{C}}$ off capacitance ${ }^{\text {d }}$ | $\mathrm{C}_{\mathrm{NO} \text { (off) }}$ $\mathrm{C}_{\mathrm{NC} \text { (off) }}$ | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{~V}$ or $\mathrm{V}+\mathrm{f}=1 \mathrm{MHz}$ | Room | - | 16 | - | pF |
| Channel-on capacitance ${ }^{\text {d }}$ | $\mathrm{Con}^{\text {a }}$ |  | Room | - | 51 | - |  |
| Power Supply |  |  |  |  |  |  |  |
| Power supply current | I+ | $\mathrm{V}_{\text {IN }}=0 \mathrm{~V}$ or $\mathrm{V}_{+}$ | Full | - | 0.00001 | 1 | $\mu \mathrm{A}$ |

## Notes

a. Room $=25^{\circ} \mathrm{C}$, full $=$ as determined by the operating suffix
b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
c. Typical values are for design aid only, not guaranteed nor subject to production testing
d. Guarantee by design, nor subjected to production test
e. $\mathrm{V}_{\mathrm{IN}}=$ input voltage to perform proper function
f. Guaranteed by 5 V leakage testing, not production tested

TYPICAL CHARACTERISTICS $\left(25^{\circ} \mathrm{C}\right.$, unless otherwise noted)

$R_{\text {ON }}$ vs. $\mathbf{V}_{\text {COM }}$ and Supply Voltage

$R_{\text {on }}$ vs. $V_{\text {COM }}$ and Temperature


Ron $_{\text {os. }}$ V. $\mathbf{V C O M}$ and Temperature

$R_{\text {ON }}$ vs. $\mathbf{V}_{\text {COM }}$ and Temperature


Leakage Current vs. Temperature


Leakage Current vs. Temperature

TYPICAL CHARACTERISTICS $\left(25^{\circ} \mathrm{C}\right.$, unless otherwise noted)


Leakage Current vs. Temperature


Supply Current vs. Temperature


Supply Current vs. Temperature


Insertion Loss, Off-Isolation Crosstalk vs. Frequency


Supply Current vs. Input Switching Frequency


Switching Time vs. Temperature and Supply Voltage

TYPICAL CHARACTERISTICS $\left(25^{\circ} \mathrm{C}\right.$, unless otherwise noted)


Switching Threshold vs. Supply Voltage


Charge Injection vs. Analog Voltage


Power Down Leakage Current vs. $\mathbf{V}_{\text {com }}$


Supply Current vs. Enable Input Voltage


Power Down Leakage Current vs. Temperature

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## TEST CIRCUITS



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.


Fig. 1 - Switching Time


Fig. 2 - Break-Before-Make Interval


IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection

## TEST CIRCUITS



Fig. 4 - Off-Isolation


Fig. 5 - Channel Off / On Capacitance

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